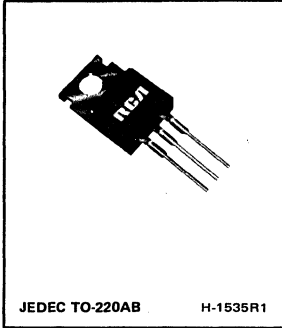


**RCA**  
Solid State  
Division

## Power Transistors

### RCA1C14

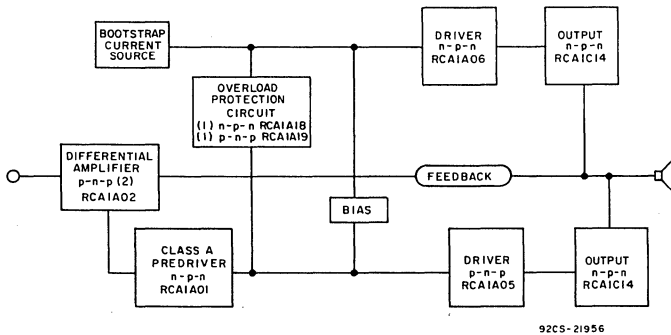


## Silicon Transistor for 25-Watt Quasi-Complementary-Symmetry Audio Amplifiers

RCA1C14 is an n-p-n homotaxial-base silicon power transistor provided in the JEDEC TO-220AB package. This device is ideally suited for use in the output stage of quasi-complementary-symmetry audio amplifiers.

The 25-watt audio-amplifier circuit shown in Figs. 1 and 5

uses two RCA1C14 transistors in conjunction with seven TO-39 low-level audio transistors, 11 diodes, and a 52-volt split supply. The amplifier output is directly coupled to an 8-ohm speaker. Ruggedness and economy are features of this high fidelity amplifier.



92CS-21956

Fig. 1— Block diagram and transistor complement for 25-watt quasi-complementary-symmetry audio amplifier.

**MAXIMUM RATINGS, Absolute-Maximum Values:**

		RCA1C14	
COLLECTOR-TO-BASE VOLTAGE .....	$V_{CBO}$	60	V
COLLECTOR-TO-EMITTER VOLTAGE:			
With base open .....	$V_{CEO}$	40	V
With external base-to-emitter resistance ( $R_{BE}$ ) = 100 $\Omega$ .....	$V_{CER}$	60	V
EMITTER-TO-BASE VOLTAGE .....	$V_{EBO}$	5	V
COLLECTOR CURRENT .....	$I_C$	7	A
BASE CURRENT .....	$I_B$	3	A
TRANSISTOR DISSIPATION:	$P_T$		
At case temperatures up to 25°C .....		50	W
At case temperatures above 25°C .....		<i>See Fig. 2</i>	
TEMPERATURE RANGE:			
Storage & Operating (Junction) .....		-65 to 150	°C
PIN TEMPERATURE (During Soldering):			
At distances $\geq 1/32$ in. (0.8 mm) from case for 10 s max. ....		230	°C

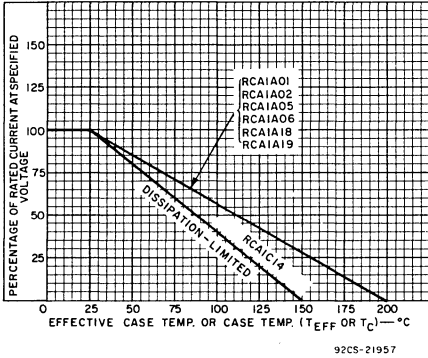


Fig. 2- Derating curves for all types.

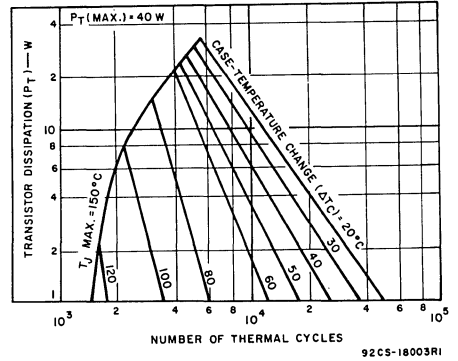


Fig. 3- Thermal-cycling ratings for RCA1C14.

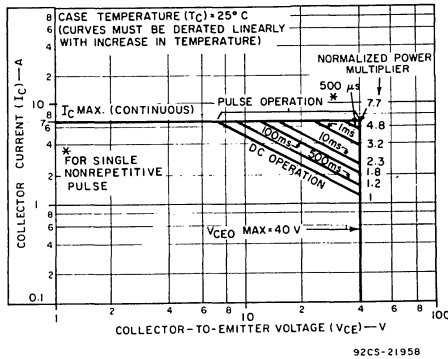
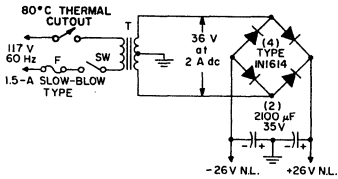
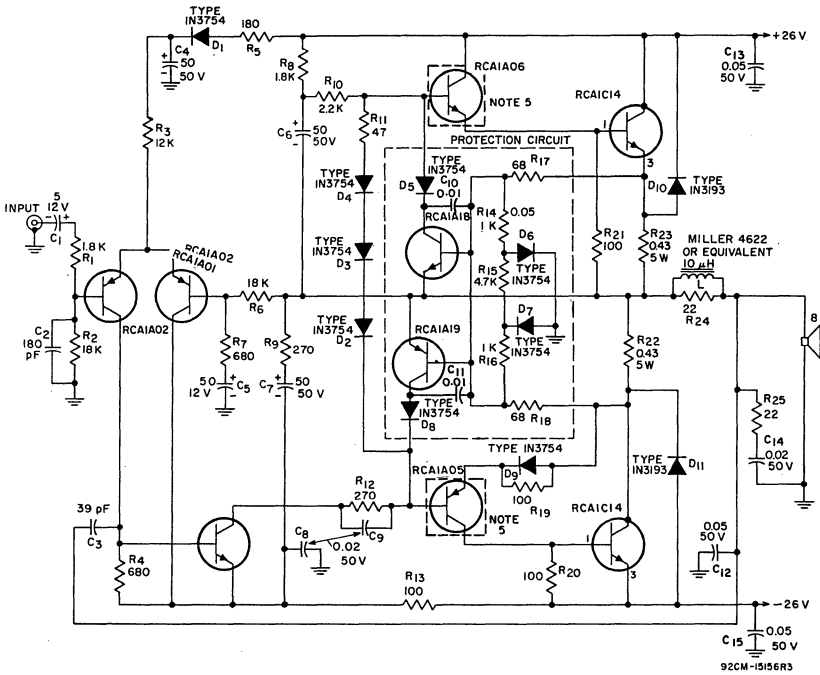


Fig. 4- Maximum operating areas for RCA1C14.



92CS-15159R2

**NOTES:**

1. T: Signal 36-2 (Signal Transformer Co., 1 Junius St., Brooklyn, N.Y. 11212), or equivalent.
2. Resistors are 1/2-watt unless otherwise specified; values are in ohms.
3. Capacitances are in  $\mu\text{F}$  unless otherwise specified.
4. Non-inductive resistors.
5. Mount driver transistors on heat sink, Wakefield No. 209-AB, or equivalent. (Alternatively, this type may be obtained with a factory-attached integral heat sink.)
6. Provide approximately  $2^{\circ}\text{W}$  heat sinking per output device.

Fig. 5—25-watt amplifier circuit featuring quasi-complementary-symmetry output.

**TYPICAL PERFORMANCE DATA  
For 25-Watt Audio Amplifier**

Measured at a line voltage of 120 V,  $T_A = 25^{\circ}\text{C}$ , and a frequency of 1 kHz, unless otherwise specified

**Power:**

Rated power (8- $\Omega$ load, at rated distortion) . . . . .	25 W
Typical power (4- $\Omega$ load) . . . . .	45 W
Typical power (16- $\Omega$ load) . . . . .	16 W
Music power (8- $\Omega$ load, at 5% THD with regulated supply) . . . . .	38 W
Dynamic power (8- $\Omega$ load, at 1% THD with regulated supply) . . . . .	33 W

**Total Harmonic Distortion:**

Rated distortion . . . . .	1.0%
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**IM Distortion:**

10 dB below continuous power output at 60 Hz and 7 kHz (4:1) . . . . .	0.1%
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**Sensitivity:**

At continuous power-output rating . . . . .	600 mV
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**Hum and Noise:**

Below continuous power output:	
Input shorted . . . . .	80 dB
Input open . . . . .	75 dB
Input Resistance . . . . .	20 k $\Omega$

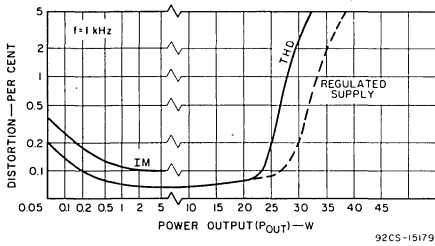


Fig.6- Distortion vs. power output.

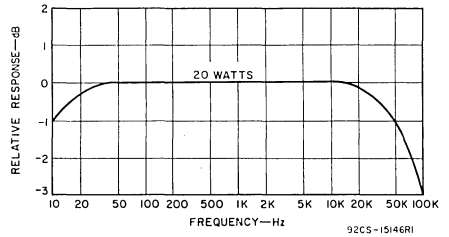


Fig.7- Response curve.

**Type RCA1C14**

Package: JEDEC TO-220AB

Construction: Silicon n-p-n, hometaxial base

ELECTRICAL CHARACTERISTICS, At Case Temperature ( $T_C = 25^\circ C$  Unless Otherwise Specified)

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS		UNITS
			MIN.	MAX.	
Collector Cutoff Current: With external base-to-emitter resistance ( $R_{BE}$ )	$I_{CER}$	$V_{CE} = 50 V, R_{BE} = 100\Omega$	-	0.5	mA
Emitter Cutoff Current: With collector open	$I_{EBO}$	$V_{EB} = 5 V, I_C = 0$	-	1	mA
Collector-to-Emitter Voltage: With base open	$V_{CEO}$	$I_C = 1 A, I_B = 0$	40	-	V
Collector-to-Emitter Voltage: With external base-to-emitter resistance ( $R_{BE}$ )	$V_{CER}$	$I_C = 0.1 A, R_{BE} = 100\Omega$	60	-	V
Gain Bandwidth Product	$f_T$	$I_C = 0.5 A, V_{CE} = 4 V$	0.8	-	MHz
DC Forward-Current Transfer Ratio	$h_{FE}$	$I_C = 3 A, V_{CE} = 4 V$	20	70	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 3 A, I_B = 0.3A$	-	1	V
Base-to-Emitter Voltage	$V_{BE}$	$I_C = 3 A, V_{CE} = 4 V$	-	1.4	V
Second-Breakdown Collector Current: With base forward biased	$I_{S/b}$	$V_{CE} = 40 V, t = 0.5 s$	1.25	-	A

For characteristics curves and test conditions, refer to published data for prototype 2N5495 (File 353).

**TERMINAL CONNECTIONS FOR TYPE RCA1C14**

- Lead 1 - Base
- Lead 2 - Collector
- Lead 3 - Emitter
- Lead 4 - Collector